

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)

Application Number	10551923
Filing Date	2005-10-03
First Named Inventor	Tomohiro Kawase
Art Unit	1722
Examiner Name	Not Yet Assigned <i>H. K. H. H.</i>
Attorney Docket Number	20239/0202145-US0

U.S. PATENTS

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<i>F.H.</i>	1	E. M. MONBERG, The Growth and Characterization of Large Size, High Quality, InP Single Crystals, Micronanoelectronic Technology, Vol. 2, pp. 55-59 , April 30, 1989	<input checked="" type="checkbox"/>
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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete If Known		
				Application Number	10/551,923	
				Filing Date	October 3, 2005	
				First Named Inventor	Tomohiro Kawase	
				Art Unit	N/A 17-22	
Examiner Name	Not Yet Assigned Hiteshew					
Sheet	1	of	1	Attorney Docket Number	20239/0202145-USO	

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F.H.	CA	International Preliminary Report on Patentability for PCT/JP2004/006427 mailed on March 23, 2006	

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Examiner Signature	<i>Hiteshew</i>	Date Considered	7/18/2007
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JC20 Rec'd PCT/PTO 03 OCT 2005

PTO/SB/08a/b (08-03)

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				Filing Date	Concurrently Herewith 10/3/2005
				First Named Inventor	Tomohiro Kawase
				Art Unit	NA 1702
				Examiner Name	Not Yet Assigned - H/Hes h u
				Attorney Docket Number	20239/0202145-USO
Sheet	1	of	2		

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FH.	AA*	US-5,647,917-A	07-15-1997	Sumitomo Electric Industries, Ltd.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
FH. ↑ ↓ FH.	BA	JP-03-237088-A	10-22-1991	Nippon Mining Co Ltd	Abstract only	✓
	BB	JP-2000-313699-A	11-14-2000	Japan Energy Corp	Abstract only	✓
	BC	JP-03-040987-A	02-21-1991	Nippon Telegr & Teleph Corp <NTT>	Abstract only	✓
	BD	JP-08-078348-A	03-22-1996	Sumitomo Electric Ind Ltd	Abstract only	✓
	BE	JP-11-302094-A	11-02-1999	Japan Energy Corp	Abstract only	✓

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FH. ↑ ↓ FH.	CA	International Search Report for PCT/JP2004/006427 mailed October 5, 2004		
	CB	P. RUDOLPH, et al., Studies on interface curvature during vertical Bridgman growth of InP in a flat-bottom container, Journal of Crystal Growth, 1996, Vol. 158, pp 43-48		
	CC	esp@cenet document view: Abstract of EP 0701008 published on March 13, 1996		
	CD	XIAOYU HU, et al., Three Inch VGF Semi-insulating InP, Post Deadline Papers, Tenth International Conference on Indium Phosphide and Related Materials (IPRM '98), May 11-15, 1998, pp. 15-16		
	CE	TOMOHIRO KAWASE, et al., Improvement of microscopic and macroscopic uniformity in 4-inch InP substrate for IC application by Vertical Boat Growth, GaAs IC Symposium, Technical Digest, October 20-23, 2002, pp. 147-150		
	CF	T. ASAHI, et al., Growth of 100mm Diameter <100> InP Single Crystals by the Vertical Gradient Freezing Method, Post Deadline Papers, Tenth International Conference on Indium Phosphide and Related Materials (IPRM '98), May 11-15, 1998, pp. 1-2		
	CG	TOSHIKAKI ASAHI, et al., Growth of 100-mm-Diameter <100> InP Single Crystals by the Vertical Gradient Freezing Method, Jpn. J. Appl. Phys. Vol. 38, February, 1999, pp. 977-980		
	CH	T. ASAHI, et al., VGF CRYSTAL GROWTH AND VAPOR-PHASE Fe DOPING TECHNOLOGIES FOR SEMI-INSULATING 100mm DIAMETER InP SUBSTRATES, 11th International Conference on Indium Phosphide and Related Materials, May 16-20, 1999, pp. 249-254		
	CI	FUMIO MATSUMOTO, et al., Growth of twin-free <100> InP single crystals by the liquid encapsulated vertical Bridgman technique, Journal of Crystal Growth 132, 1998, pp. 348-350		
	CJ	E.M. MONBERG, et al., THE DYNAMIC GRADIENT FREEZE GROWTH OF InP, Journal of Crystal Growth 94, 1989, pp. 109-114		

Examiner Signature	<i>[Signature]</i>	Date Considered	2/18/2006
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JC20 Rec'd PCT/PTO 03 OCT 2005

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